

DLA11C

Silicon Diffused Junction Type

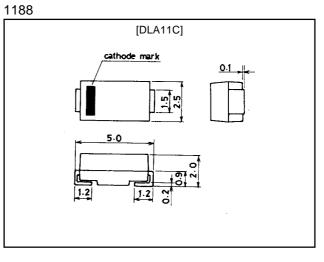
# **1.1A Ultrahigh-Speed Rectifier**

### **Features**

- Supports automatic mounting and permits DLA11Capplied sets to be made smaller.
- $\cdot$  Fast reverse recovery time and small switching loss.
- · Peak reverse voltage :  $V_{RM}$ =200V.
- · Average rectified current :  $I_O=1.1A$ .

# **Package Dimensions**

unit:mm



# **Specifications**

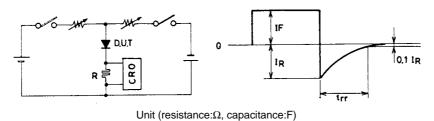
### Absolute Maximum Ratings at Ta = 25°C

| Parameter                 | Symbol | Conditions  | Ratings     | Unit |
|---------------------------|--------|---|-------------|------|
| Peak Reverse Voltage      | VRM    |   | 200         | V    |
| Average Rectified Current | lo     | 50Hz sine wave, mounted on alumina board          | 1.1         | A    |
|                           |        | Resistive load resistor, mounted on PCB           | 0.84        | A    |
| Surge Forward Current     | IFSM   | 50Hz sine wave, nonrepetitive, 1 cycle peak value | 30          | A    |
| Junction Temperature      | Tj     |   | 150         | °C   |
| Storage Temperature       | Tstg   |   | -55 to +150 | °C   |

#### **Electrical Characteristics at Ta = 25°C**

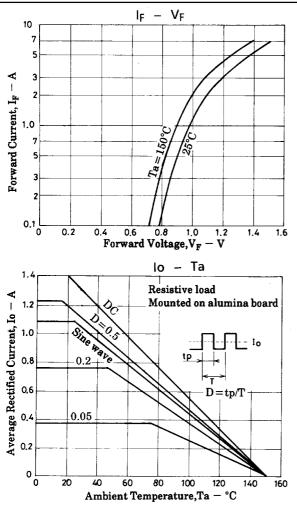
| Parameter             | Symbol         | Conditions                                | Ratings |     |      | Unit |
|-----------------------|----------------|---|---------|-----|------|------|
|                       |                |   | min     | typ | max  | Onit |
| Forward Voltage       | V <sub>F</sub> | I <sub>F</sub> =1.1A                      |         |     | 0.98 | V    |
| Reverse Current       | IR             | V <sub>R</sub> =200V                      |         |     | 10   | μA   |
| Reverse Recovery Time | trr            | I <sub>F</sub> =0.5A, I <sub>R</sub> =1A  |         |     | 50   | ns   |
| Thermal Resistance    | θj–l           | Junction-Lead                             |         |     | 23   | °C/W |
|                       | өј–а           | Junction-Ambient Mounted on alumina board |         |     | 108  | °C/W |
|                       |                | Mounted on PCB                            |         |     | 157  | °C/W |

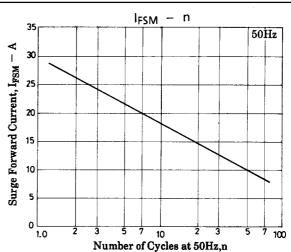
#### **Reverse Recovery Time Test Circuit**



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